

1. TYPE LSK3019 FP8
2. STRUCTURE SILICON N-CHANNEL MOS FET
3. APPLICATIONS SWITCHING
4. ABSOLUTE MAXIMUM RATINGS [Ta=25°C]

DRAIN-SOURCE VOLTAGE	VDSS . . .	30V
GATE-SOURCE VOLTAGE	VGSS . . .	±20V
DRAIN CURRENT CONTINUOUS	ID . . .	±100mA
PULSED	IDP . . .	±400mA PW ≤ 10 μS DUTY CYCLE ≤ 1%
TOTAL POWER DISSIPATION	PD . . .	150mW

EACH TERMINAL MOUNTED ON A RECOMMENDED LAND

CHANNEL TEMPERATURE	Tch . . .	150°C
RANGE OF STORAGE TEMPERATURE	Tstg . . .	-55~150°C

5. THERMAL RESISTANCE

CHANNEL TO AMBIENT	Rth(ch-a) . . .	833°C/W
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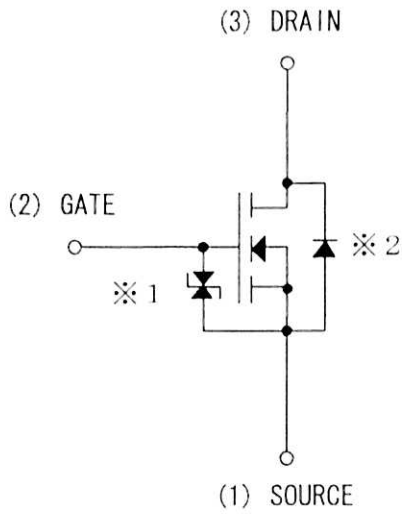
EACH TERMINAL MOUNTED ON A RECOMMENDED LAND

DESIGN	CHECK	APPROVAL	DATE: 13/MAR/2007	SPECIFICATION No. : T837-LSK3019 FP8
<i>J. Arizono</i>	<i>A. Tsubaki</i>	<i>S. Higashida</i>	REV. 0	ROHM CO., LTD.

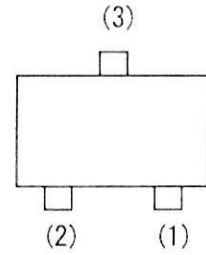
6. ELECTRICAL CHARACTERISTICS [Ta=25°C]

PARAMETER	ITEM	CONDITION	MIN.	TYP.	MAX.
GATE-SOURCE LEAKAGE	IGSS	VGS=±20V/VDS=0V			±1 μA
DRAIN-SOURCE BREAKDOWN VOLTAGE	V(BR)DSS	ID=10 μA/VGS=0V	30V		
ZERO GATE VOLTAGE DRAIN CURRENT	IDSS	VDS=30V/VGS=0V			1 μA
GATE THRESHOLD VOLTAGE	VGS(th)	VDS=3V/ID=100 μA	0.8V		1.5V
STATIC DRAIN-SOURCE ON-STATE RESISTANCE	RDS(on)	ID=10mA/VGS=4V		5 Ω	8 Ω
		ID=1mA/VGS=2.5V		7 Ω	13 Ω
FORWARD TRANSFER ADMITTANCE	Yfs	VDS=3V/ID=10mA	20mS		
INPUT CAPACITANCE	Ciss	VDS=5V/VGS=0V f=1MHz		13pF	
OUTPUT CAPACITANCE	Coss			9pF	
REVERSE TRANSFER CAPACITANCE	Crss			4pF	
TURN-ON DELAY TIME	td(on)				15ns
RISE TIME	Tr	ID=10mA/VDD≐5V VGS=5V/RL=500 Ω RG=10 Ω		35ns	
TURN-OFF DELAY TIME	td(off)			80ns	
FALL TIME	tf			80ns	

7. INNER CIRCUIT

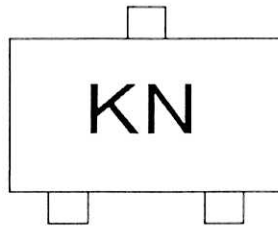


(1) SOURCE
(2) GATE
(3) DRAIN



※ 1 ESD PROTECTION DIODE
※ 2 BODY DIODE

8. MARKING



"KN" MEANS LSK3019 FP8.